

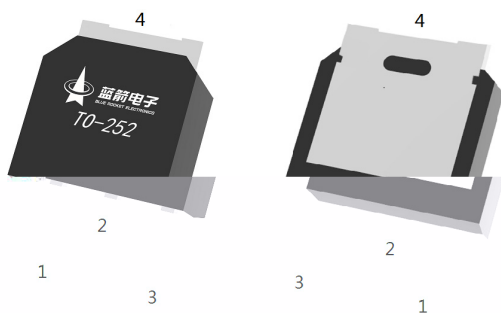
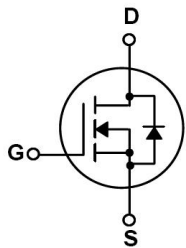
Rev.A Feb.-2023

TO-252 N
 N-CHANNEL MOSFET in a TO-252 Plastic Package.

$R_{DS(on)}$ C_{rss}
 Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products, Meet the stringent requirements of automotive applications.



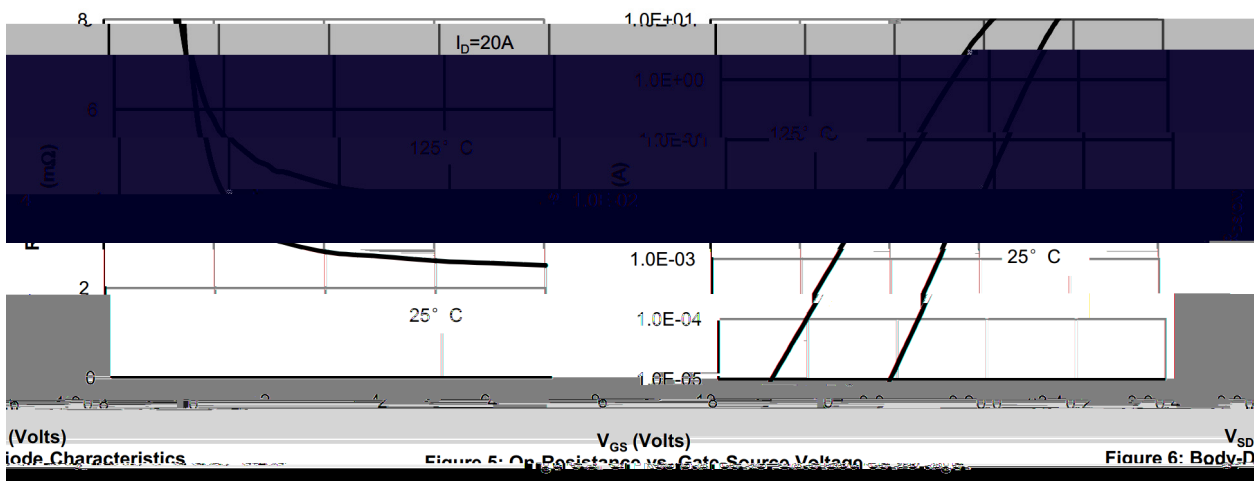
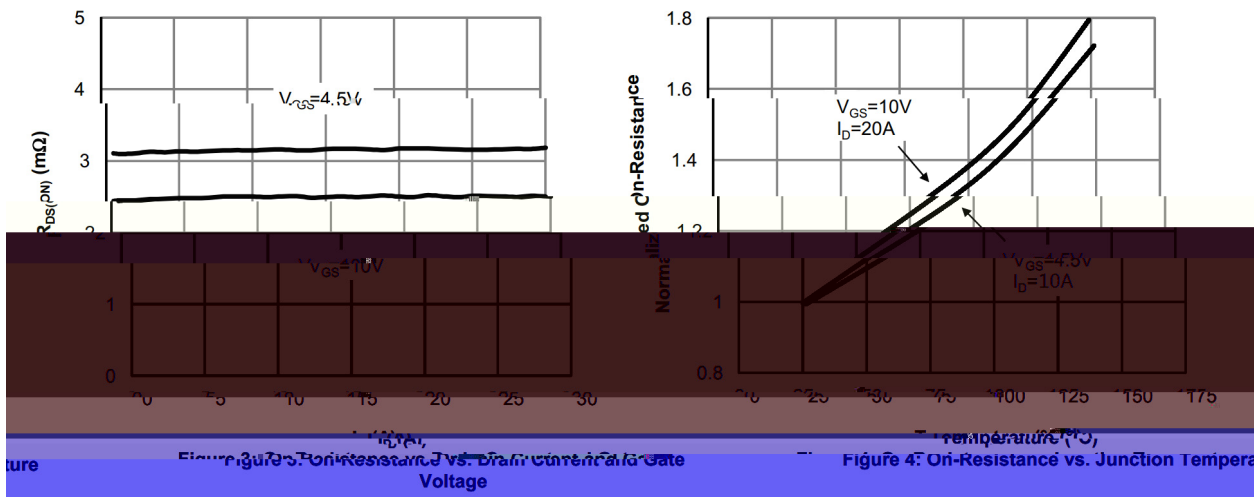
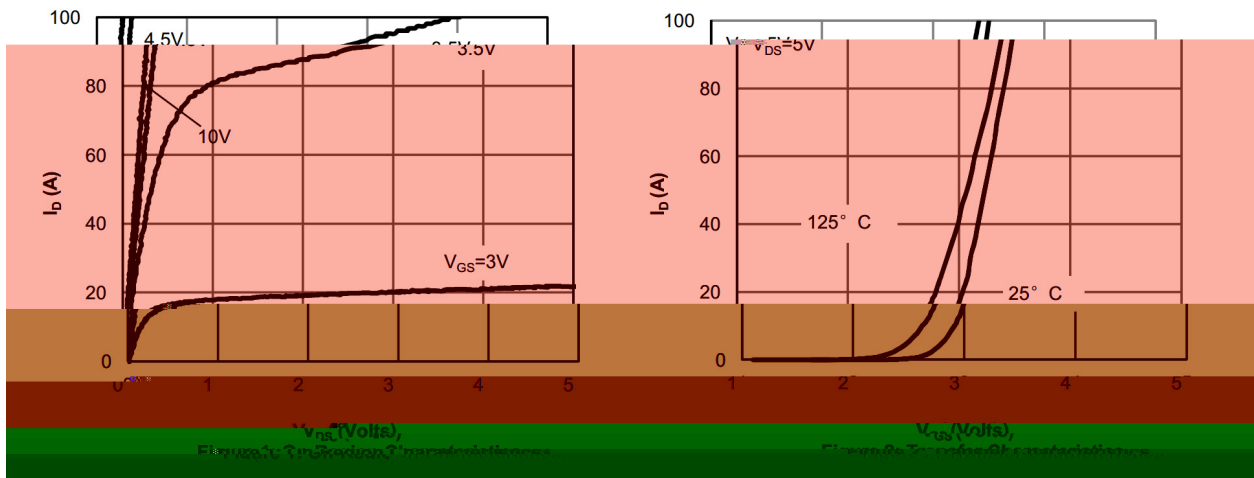
PIN1 G PIN 2 D PIN 3 S PIN 4 D

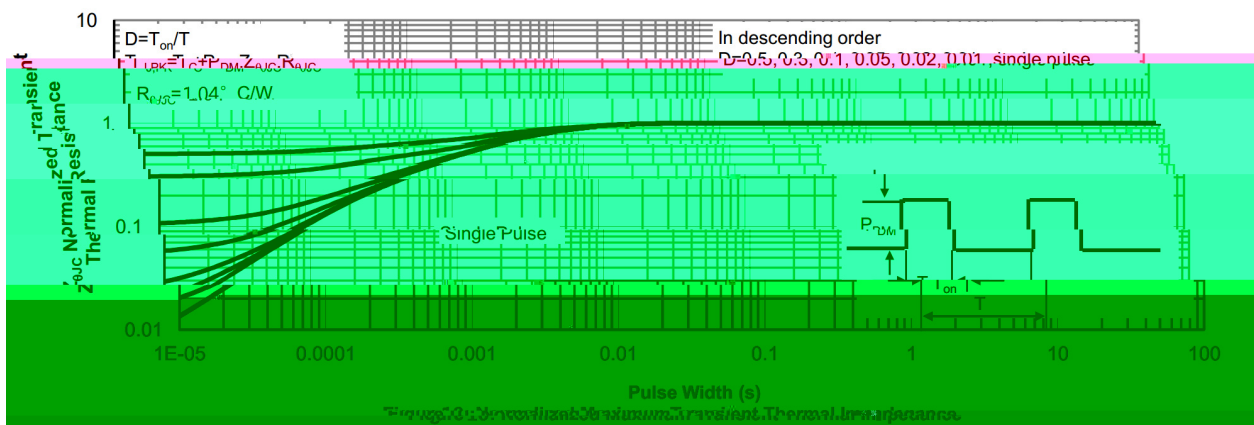
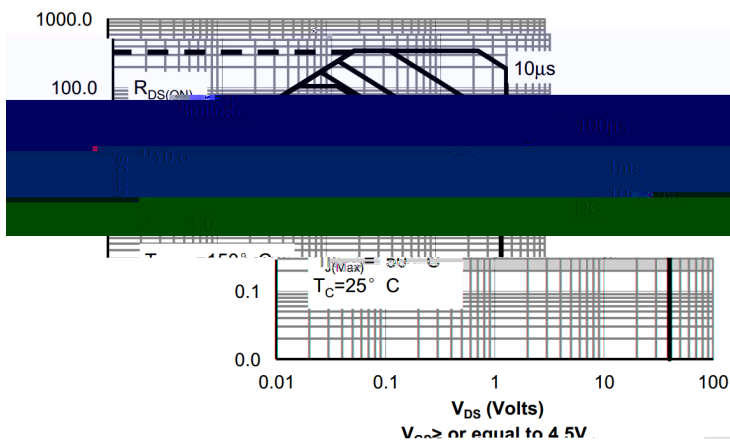
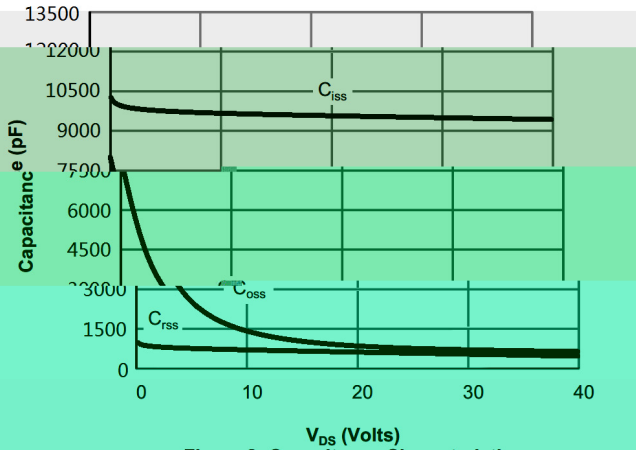
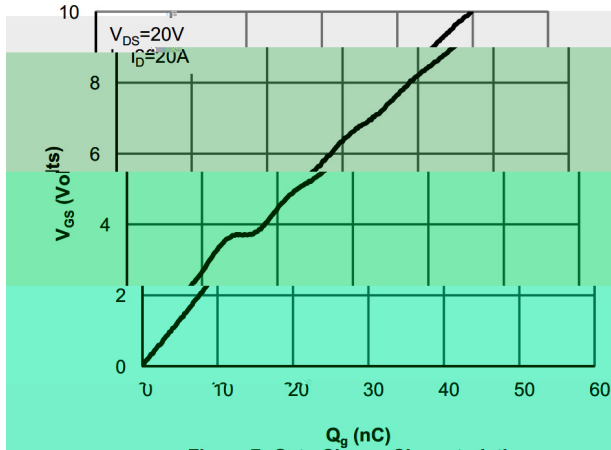
See Marking Instructions.

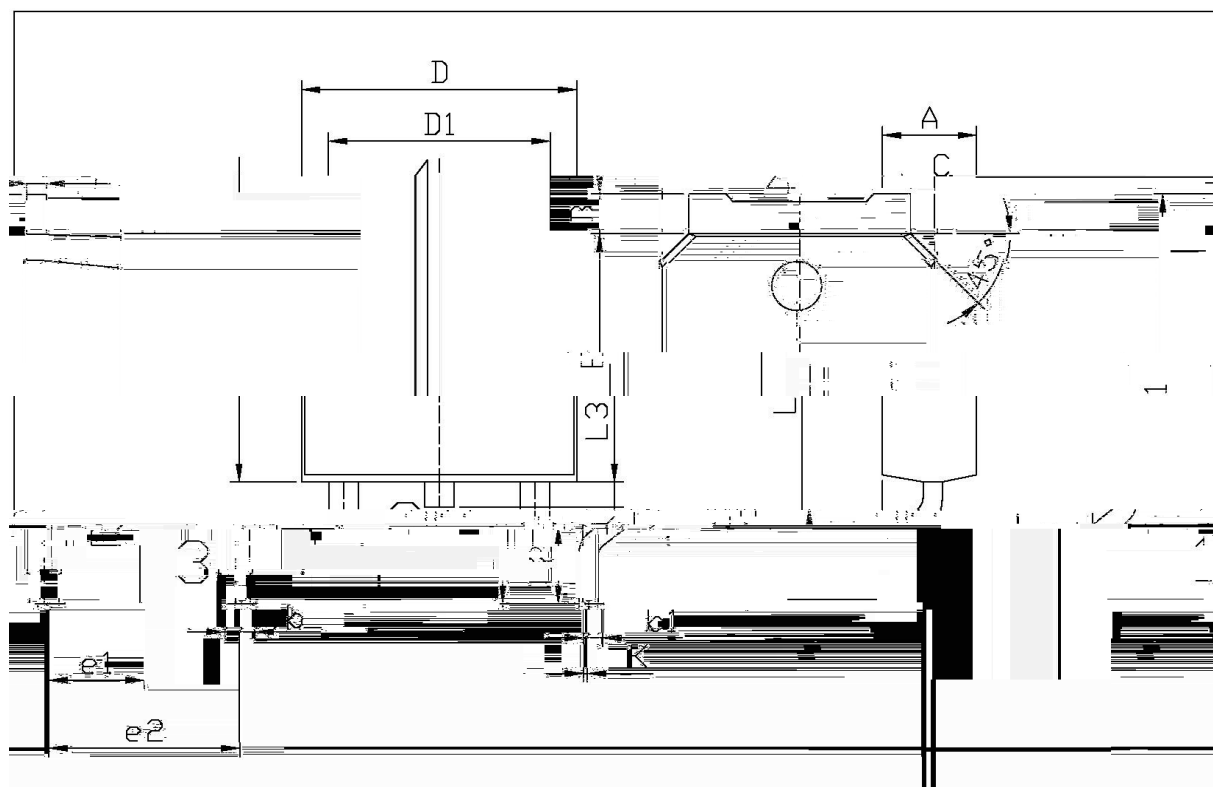
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Drain Current		$I_D(T_C=25^\circ\text{C})$	150	A
Drain Current - Pulsed		I_{DM}	304	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	33	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	435	mJ
Power Dissipation		$P_D(T_C=25^\circ\text{C})$	120	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	20	/W
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.04	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		2.5	3.0	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		3.1	5.0	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.4	V
Gate resistance	R_g	$V_{GS}=0V$ $f=1MHz$ $V_{DS}=0V$		1.16		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		9600		pF
Output Capacitance	C_{oss}			740		
Reverse Transfer Capacitance	C_{rss}			650		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=20A$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			13.2		
Gate Drain Charge	Q_{gd}			3.1		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=1\Omega$ $R_{GEN}=3\Omega$		11		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			10		



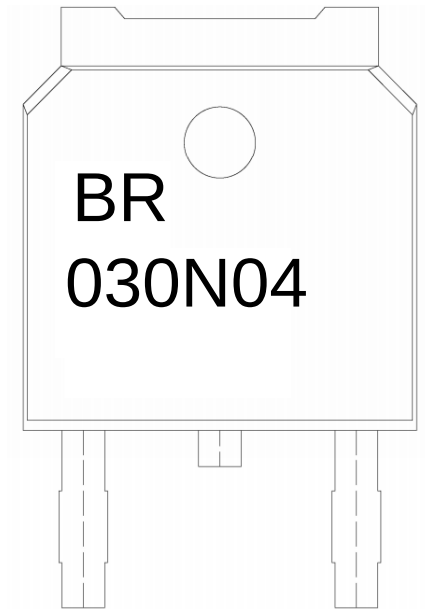




单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
6.25	A	2.20	2.40	E	5.95
2.34	B	0.95	1.25	e1	2.24
4.72	C	0.70	0.90	e2	4.62
L1	9.85	10.35	b1	0.45	0.55
L3	0.45	0.55	L2	1.30	2.00
5.50	K	0.00	0.10	D1	5.10

T0-252



BR

030N04

Note:

BR: Company Code

030N04: Product Type Code

****: Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)

- 1

150 180

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10

/sec.
- Note:

1.Preheating:150~180 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL